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Bruce D. Marchant Pean Probst, Paul Thorup, and Densen Cao

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#### IN THE DRAWINGS:

Please include the Figure 2C to the present application.

#### **REMARKS**

Upon entry of this amendment, which amends claims \*\*\*\* and adds claims \*\*\*\*, claims \*\*\*\* remain pending. In the October 25, 2000 Office Action, the drawings were objected to under 37 C.F.R. § 1.83(a); claims 1-17 were rejected under 35 U.S.C. § 102(b) as being anticipated by the Background section (pp. 1-2, Fig. 1) of the present application; and claims 9, 11, 15 and 17 were rejected under 35 U.S.C. 103(a) as being unpatentable over the Background section (pp. 1-2, Fig. 1) of the present application. Applicant respectfully requests reconsideration of the claims in view of the above amendments and the comments below.

## Object to the Drawings

In the October, 2000 Office Action, the Examiner objected to the drawings under 37 C.F.R. § 1.83(a) for not showing every feature of the invention specified in the claims. More specifically, the Examiner stated that "the slanted edge along the etched side of the source region", as claimed in claim 12, "must be shown in Figs 2A-2B and Fig. 4."

In response, Applicants have attached a new figure, Fig. 2C, which shows this slanted source edge aspect of the invention and have amended the specification to specify that this aspect of the invention is an alternative embodiment to that shown in Fig. 2B. Support for this aspect of the invention is provided in the first full paragraph on page 7 of the application.

Applicants believe that Fig. 2B requires no modification, since that figure illustrates a structure prior to the step of etching the trenched heavy body, during which step the slanted edge along the source region is formed. Fig. 4, as supported by page 7, lines 25-28 of the application, already shows this aspect of the invention. Therefore, Applicants respectfully believe that no modification of this figure is required.

No new matter has been introduced by the addition of Fig. 2C. Accordingly, Applicants respectfully request that the objection to the drawings be removed.



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## Rejections Under 35 U.S.C. § 102(b) - Claims 1-17

In the Office Action, the Examiner rejected claims 1-17 under 35 U.S.C. § 102(b) as being anticipated by the Background section (pp. 1-2, Fig. 1) of the present application. For the following reasons, Applicants respectfully believe that these rejections cannot be legitimately maintained.

To qualify for an anticipatory reference with regard to a specific claim, all elements and limitations of the claim must be disclosed in the reference.

The Examiner asserts that all the claim elements and limitations of claims 1 and 13 are disclosed in the Background section (pp. 1-2, Fig. 1) of the present application. More specifically, the Examiner's basis for rejection of claims 1-17 is stated on pages 2-3 as follows:

"Applicant's Application Background, pages 1-2 and Fig. 1, disclosees [sic] a process for manufacturing a trench field effect transistor comprising the steps of:

etching a first trench in a substrate having a first conductivity type; lining the first trench with a layer of dielectric material; substantially filling the trench with conductive material to forma gate electrode of the field effect transistor;

implanting impurities of a second conductivity type into the substrate to form a body region having the second conductivity type over the substrate;

implanting impurities of the first conductivity type inside the body region to form a source region adjacent to the first trench;

etching a second trench through the source region and into the body region;

and filling the second trench with conductive material for making contact with both the source and the body region.

Applicants respectfully disagree. The trenches described in the Background section of the application are gate trenches. As described on page 1, lines 14-17, and as shown in Figure 1, a gate trench has a dielectric layer, which lines the trench, and a conductive material that fills the dielectric-lined trench. The dielectric layer prevents the conductive material from contacting the body region of the trench field effect transistor.

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The "first trench" recited in both independent claims 1 and 13 are gate trenches, since it is used to form a gate electrode for the trench field effect transistor. The gate electrode is formed by the first three steps of the methods claimed in claims 1 and 13. Specifically, formation of the gate electrode in claim 1 comprises the first three steps of claim 1:

"forming a first trench extending into the substrate; lining the first trench with dielectric material; [and] substantially filling the first trench with conductive material to form a gate electrode of the field effect transistor...."

Claim 13 recites substantially similar steps to form a gate electrode.

By contrast, the "second trench" in independent claims 1 and 13 are <u>not</u> gate trenches. Rather, they are trenches that accommodate the heavy body region of the transistor. Regarding claim 1 in particular, the heavy body region is formed in the last two steps:

"forming a second trench adjacent to said source region and extending into the body region below the source region; and filling the second trench with high conductivity material for making contact to the body region."

(emphasis supplied).

Claim 13 recites substantially similar steps to form a trenched body region.

From the foregoing observations, it is clear that the gate trenches shown in the Background section of the present application are not trenches that accommodate a heavy body region. The highlighted portion of the excerpt from claim 1 above highlights the distinction between the two. The conductive material formed in the "second trench" makes contact to the body region but the conductive material in the gate trenches (Background section) does not. Therefore, because the last two steps recited in claims 1 and 13 are not taught in the Background section of the invention, the Background section of the present invention does not anticipate either of claim 1 or claim 13. Accordingly, independent claims 1 and 13 are believed to be in a condition for allowance.



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The Examiner has provided no reason why any of claims 2-12, which depend from independent claim 1, and claims 14-17, which depend from claim 13, are anticipated. It appears that the Examiner has only examined independent claims 1 and 13. Nevertheless, in light of the above arguments, which Applicants believe demonstrate the allowability of independent claims 1 and 13, these dependent claims should also be in a condition for allowance as they depend from allowable base claims.

# Rejections Under 35 U.S.C. § 103(a) - Claims 9, 11, 15 and 17

In the Office Action, the Examiner also rejected claims 9, 11, 15 and 17 under 35 U.S.C. § 103(a) as being unpatentable over the Background section (pp. 1-2, Fig. 1) of the present application. For the following reasons, Applicants respectfully disagree.

As an initial matter, because claims 9, 11, 15 and 17 each depend from what Applicants believe to be allowable base claims (claims 1 and 13), it follows that claims 9, 11, 15 and 17 should also be in a condition for allowance

Nevertheless, Applicants believe that the Examiner's reliance on <u>In re Aller</u> is inappropriate. <u>In re Aller</u> set forth the rule that "the discovery of an optimum value of a variable in a *known process* is normally obvious." (emphasis supplied). It should be realized that the processes claimed in claims 1 and 13 were <u>not known processes</u> prior to conception of the present invention. Therefore, Applicants respectfully believe that <u>In re Aller</u> is inapposite.

Finally, even if <u>In re Aller</u> were apposite, Applicants believe that the claimed depth of the heavy body trench ("second trench"), relative to the depth of the gate trench ("first trench") is not obvious when this depth is viewed in the context of the claimed process as a whole. Each of claims 9, 11, 15 and 17 depend from either of independent claims 1 and 13, each of which described above are believed novel in view of the prior art. Part of the novelty of the claimed invention is the formation of a "second trench" to implement a heavy body region. The prior art does not teach this. And, therefore, it cannot be said that the claimed depth of the gate trench relative to the heavy body trench, as claimed in claims 9, 11, 15 and 17 is obvious.



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For the foregoing reasons, therefore, Applicants believe that the 35 U.S.C. § 103(a) rejections of claims 9, 11, 15 and 17 cannot be maintained and, therefore, respectfully request that the rejections of these claims be withdrawn.

## **CONCLUSION**

In view of the foregoing, Applicants believe all claims now pending in this Application are in condition for allowance. The issuance of a formal Notice of Allowance at an early date is respectfully requested.

If the Examiner believes a telephone conference would expedite prosecution of this application, please telephone the undersigned at 415-576-0200.

Respectfully submitted,

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